BAV70

Silicon Epitaxial Planar Switching Diode

FEATURES

Small package

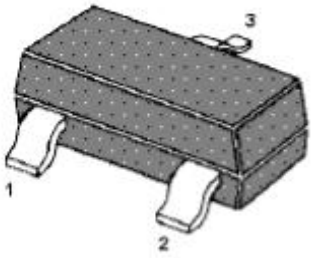
Low forward voltage

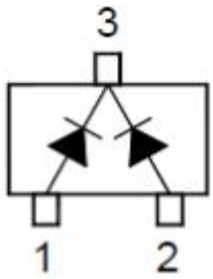
Fast reverse recovery time

Small total capacitance

APPLICATIONS

Ultra high speed switching application





Marking Code: **A4**

SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25℃)

PARAMETER		SYMBOL	VALUE	UNIT
Maximum Peak Reverse Voltage		V_{RM}	100	V
Reverse Voltage		V_R	75	V
Average Forward Current		I_o	200	mA
Maximum Peak Forward Current		I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current	at t = 1 s	I_{FSM}	1	A
Power Dissipation		P_d	350	mW
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	- 55 to + 150	℃

Characteristics at T_a = 25℃

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50mA at I_F = 150 mA	V_F	-	 715 855 1 1.25	 mV mV V V
Reverse Current at V_R = 20 V at V_R = 75 V at V_R = 25 V, T_J = 150℃ at V_R = 75 V, T_J = 150℃	I_R	-	 25 2.5 30 50	 nA μA μA μA
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V
Total Capacitance at V_R = 0 , f = 1 MHz	C_T	-	2	pF
Reverse Recovery Time at I_F = I_R = 10 mA to I_{rr} = 1mA, R_L = 50 Ω	t_{rr}	-	4	ns

BAV70

Silicon Epitaxial Planar Switching Diode

RATINGS AND CHARACTERISTIC CURVES BAV70

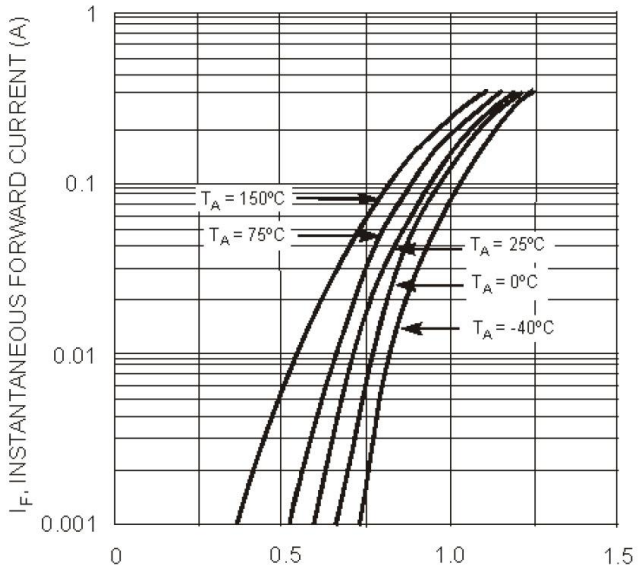


Fig. 1 Forward Characteristics

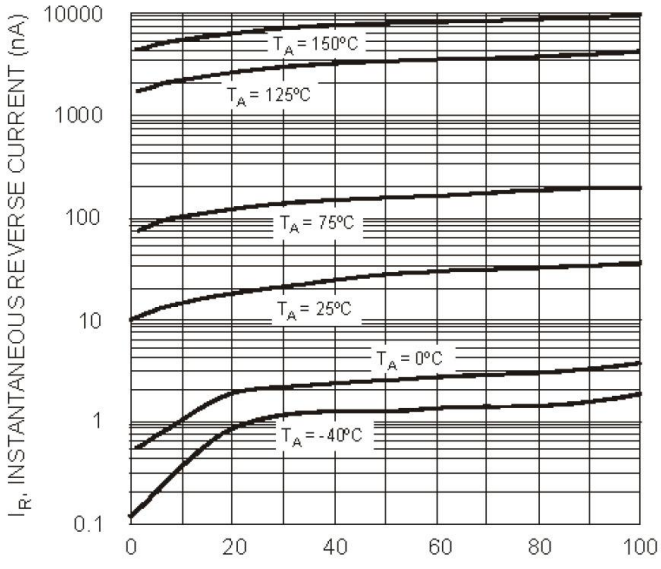


Fig. 2 Typical Reverse Characteristics

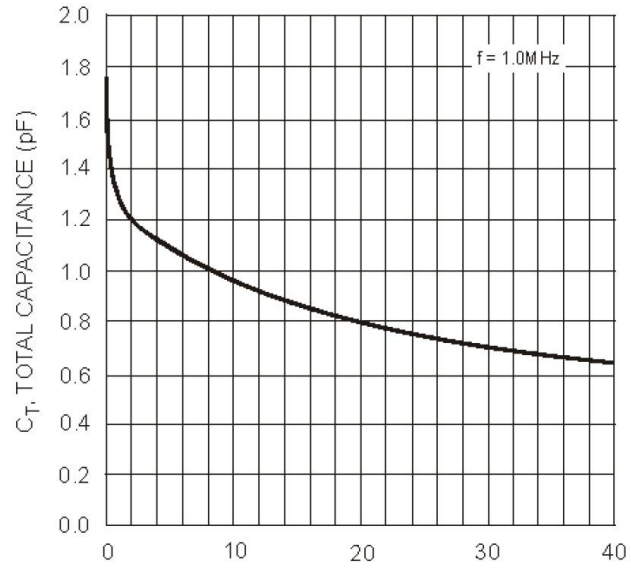


Fig. 3 Typical Capacitance vs. Reverse Voltage

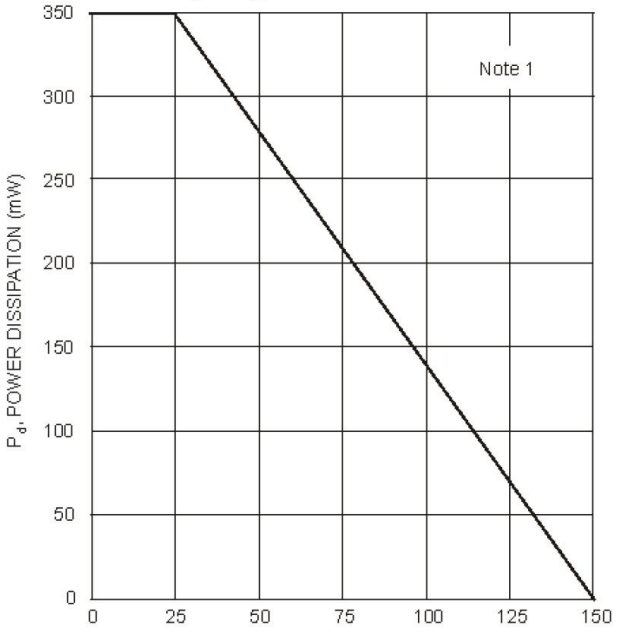


Fig. 4 Power Derating Curve

Note: Specifications are subject to change without notice.